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Nanotechnology and Microelectronics: Materials, Processing, Measurement, and Phenomena

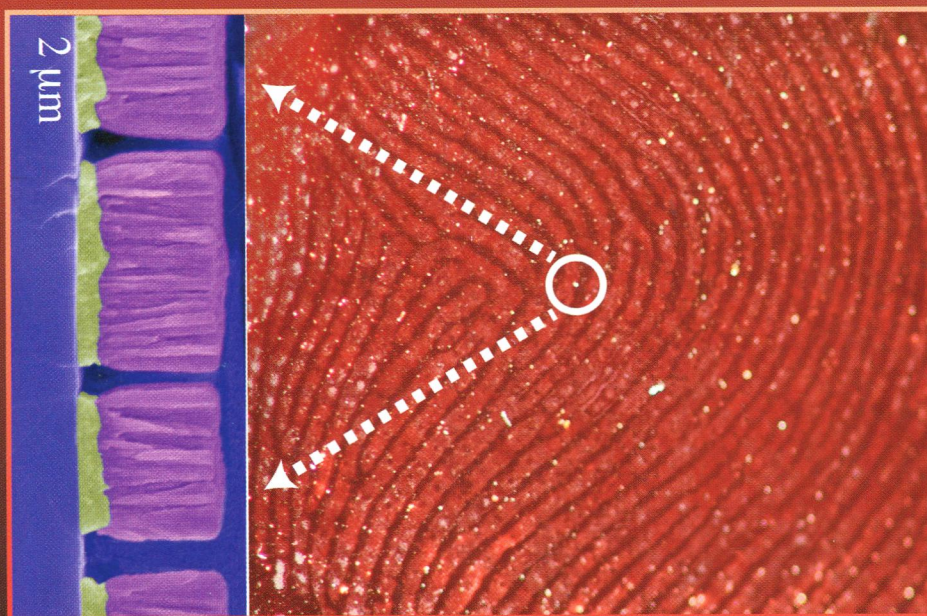


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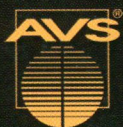
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Heusler Nanoparticles for Spintronics and Ferromagnetic Shape Memory Alloys

-by Changhai Wang, Judith Meyer, Niclas Teichert, Alexander Auge, Elisabeth Rausch, Benjamin Balke, Andreas Hütten, Gerhard H. Fecher, and Claudia Felser

Papers from the 26th International Vacuum Nanoelectronics Conference
Papers from the 30th North American Conference on Molecular Beam Epitaxy



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Second Series
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